

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-20V	112mΩ@-4.5V	-3.0A
	142mΩ@-2.5V	

## Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance

## Application

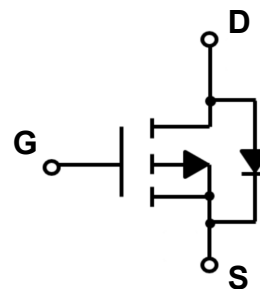
- Load Switch for Portable Devices
- DC/DC Converter

## Package

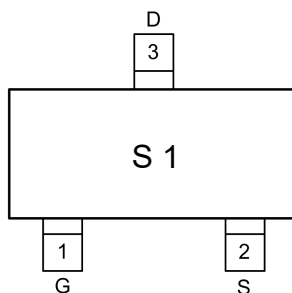


SOT-23

## Circuit diagram



## Marking



**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±8	V
Continuous Drain Current	I <sub>D</sub>	-3.0	A
Pulsed Drain Current	I <sub>DM</sub>	-10	A
Power Dissipation	P <sub>D</sub>	0.4	W
Junction Temperature	T <sub>J</sub>	-55 ~ +150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

**Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)**

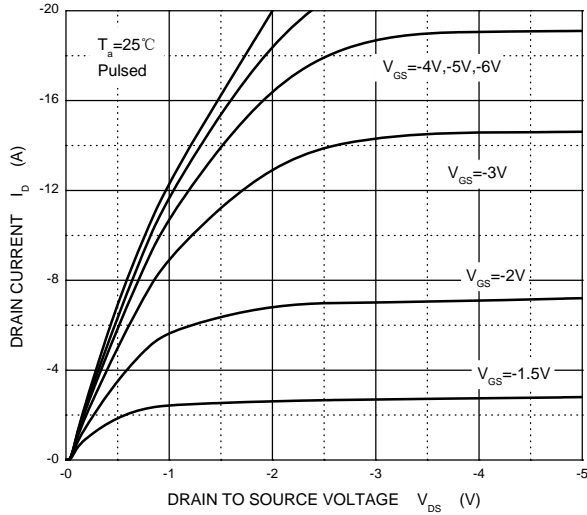
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.4		-1.0	V
Drain-source on-resistance <sup>1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.8A		90	112	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A		110	142	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz		500		pF
Output Capacitance	C <sub>oss</sub>			120		
Reverse Transfer Capacitance	C <sub>rss</sub>			80		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.0A		6.6		nC
Gate-Source Charge	Q <sub>gs</sub>			1.0		
Gate-Drain Charge	Q <sub>gd</sub>			1.4		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1A, R <sub>GEN</sub> = 2.5Ω		11		nS
Turn-on rise time	t <sub>r</sub>			12		
Turn-off delay time	t <sub>d(off)</sub>			19		
Turn-off fall time	t <sub>f</sub>			30		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current <sup>1)</sup>	I <sub>S</sub>				-3.0	A
Diode Forward voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -0.7A			-1.2	V

Notes:

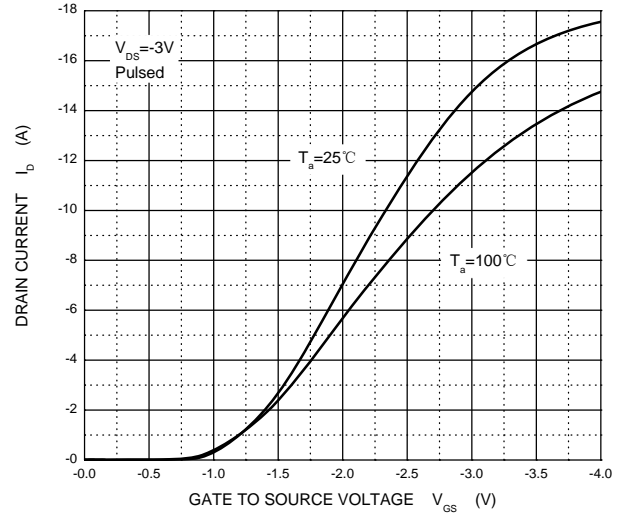
- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

## Typical Characteristics

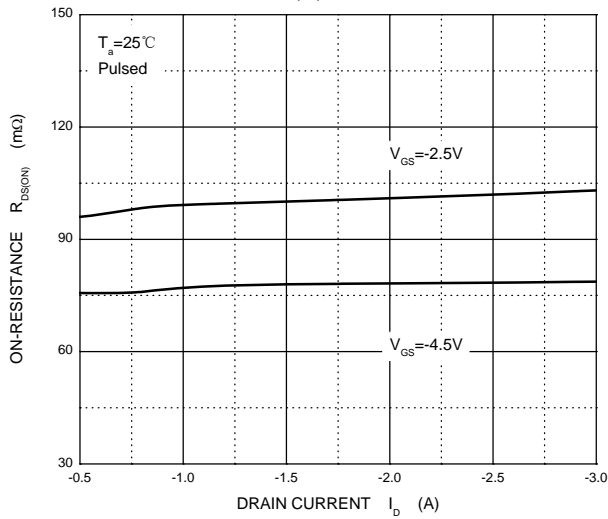
**Output Characteristics**



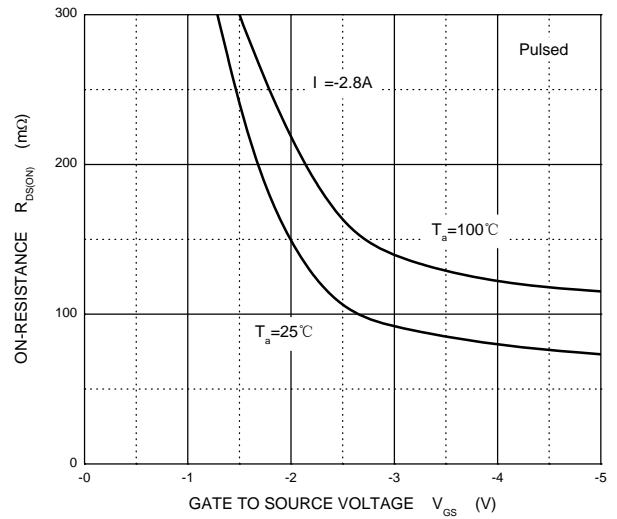
**Transfer Characteristics**



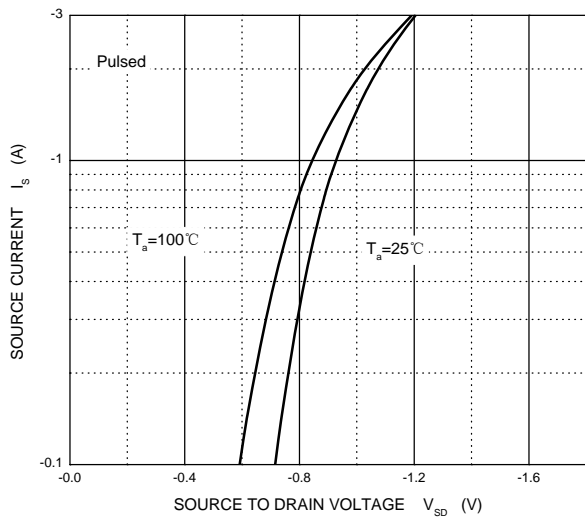
**$R_{DS(ON)}$  —  $I_D$**



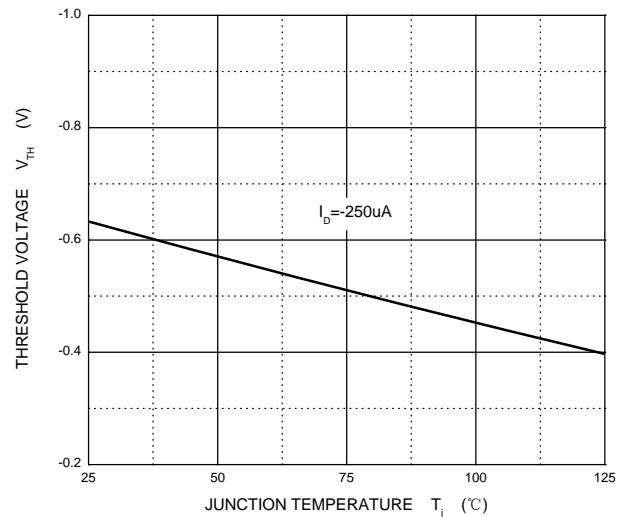
**$R_{DS(ON)}$  —  $V_{GS}$**



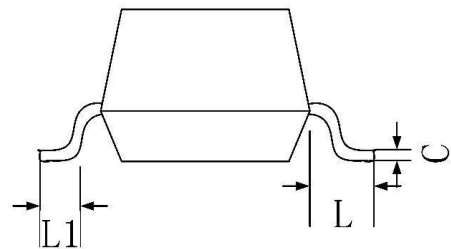
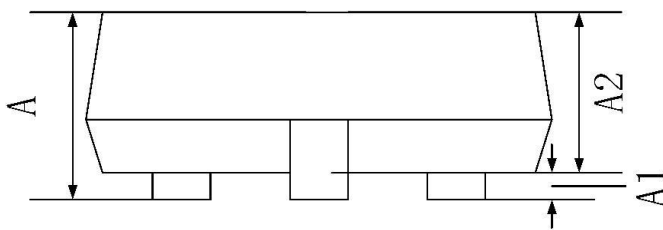
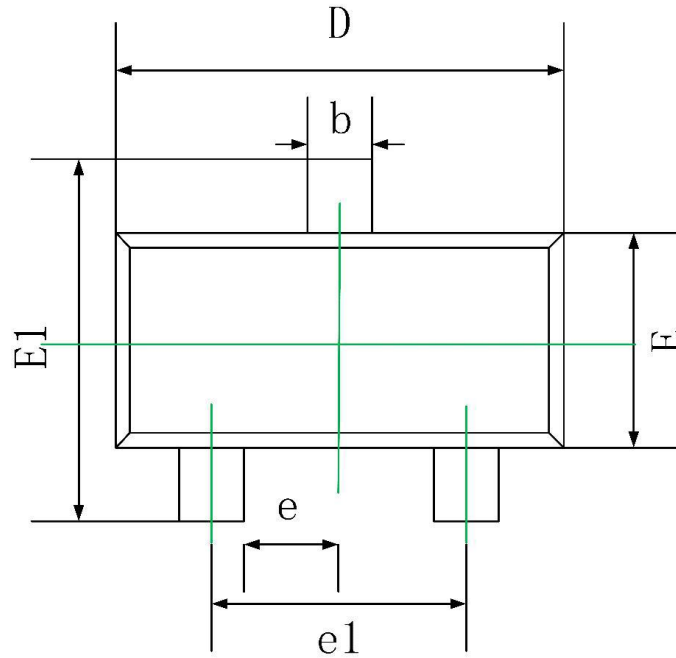
**$I_S$  —  $V_{SD}$**



**Threshold Voltage**



**SOT-23 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020